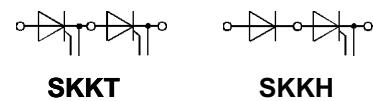


SKKT/H 213, SKKT/H 253

| V_{RSM} | V_{RRM} | $(dv/dt)_{cr}$ | I _{TRMS} (maximum values for continuous operation) | | | |
|-----------|-----------|----------------|---|--------------------------------|------------------|--------------------------------|
| | | | 370 A | 420 A | 370 A | 420 A |
| V | V | V/ μ s | I _{TAV} (sin. 180°; T _{case} = 85 °C) | | | |
| | | | 230 A | 253 A | 230 A | 250 A |
| 900 | 800 | 500 | SKKT 213/08 D | SKKT 253/08 D | SKKH — | SKKH 253/08 D |
| 1300 | 1200 | 1000 | 213/12 E | 253/12 E | 213/12 E | 253/12 E |
| 1500 | 1400 | 1000 | 213/14 E | 253/14 E | 213/14 E | 253/14 E |
| 1700 | 1600 | 1000 | 213/16 E | 253/16 E | 213/16 E | 253/16 E |
| 1900 | 1800 | 1000 | 213/18 E | 253/18 E | 213/18 E | 253/18 E |

SEMIPACK® 3
Thyristor / Diode ModulesSKKT 213 SKKH 213
SKKT 253 SKKH 253

Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Chip soldered on direct copper bonded Al₂O₃ ceramic
- Thyristor with amplifying gate
- UL recognized, file no. E 63 532

Typical Applications

- DC motor control (e.g. for machine tools)
- Temperature control (e.g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

| Symbol | Conditions | SKKT 213 SKKH 213 | SKKT 253 SKKT 253 | Units |
|------------------------------------|--|-------------------------------------|----------------------|------------------|
| I _{TAV} | sin. 180°; (T _{case} = ...) | 213 (90°C) | 253 (85°C) | A |
| I _D | B2/B6 T _{amb} = 35 °C | 354/456 | 387/502 | A |
| I _{RMS} | W1/W3 P 16/200 F | 425/3 x 360 | 465/3 x 400 | A |
| I _{TSM} | T _{vj} = 25 °C; 10 ms | 8 500 | 9 000 | A |
| i ² t | T _{vj} = 130 °C; 10 ms | 7 500 | 8 000 | A |
| | T _{vj} = 25 °C; 8,3 ... 10 ms | 361 000 | 405 000 | A ² s |
| | T _{vj} = 130 °C; 8,3 ... 10 ms | 281 000 | 320 000 | A ² s |
| t _{gd} | T _{vj} = 25 °C; I _G = 1 A | 1 | | μs |
| | dI _G /dt = 1 A/ μ s | 2 | | μs |
| t _{gr} | V _D = 0,67 · V _{DRM} | | | |
| (di/dt) _{cr} | T _{vj} = 130 °C | 250 | | A/ μ s |
| t _q | T _{vj} = 130 °C | typ. 50 ... 150 | | μs |
| I _H | T _{vj} = 25 °C; typ. / max. | 150 / 500 | | mA |
| I _L | T _{vj} = 25 °C; R _G = 33 Ω; typ. / max. | 0,3 / 2 | | A |
| V _T | T _{vj} = 25 °C; I _T = 750 A | max. 1,9 | max. 1,7 | V |
| V _{T(TO)} | T _{vj} = 130 °C | 0,95 | 0,85 | V |
| r _T | T _{vj} = 130 °C | 1,3 | 1,1 | mΩ |
| I _{DD} ; I _{RD} | T _{vj} = 130 °C; V _{RD} = V _{RRM} | 50 | 50 | mA |
| | V _{DD} = V _{DRM} | | | |
| V _{GT} | T _{vj} = 25 °C; d.c. | 3 | | V |
| I _{GT} | T _{vj} = 25 °C; d.c. | 200 | | mA |
| V _{GD} | T _{vj} = 130 °C; d.c. | 0,25 | | V |
| I _{GD} | T _{vj} = 130 °C; d.c. | 10 | | mA |
| R _{thjc} | cont. | 0,11 / 0,055 | | °C/W |
| | sin. 180 | 0,115 / 0,057 | | °C/W |
| | rec. 120 | 0,125 / 0,0625 | | °C/W |
| R _{thch} | per thyristor / | 0,08 / 0,04 | | °C/W |
| T _{vj} , T _{stg} | per module | – 40 ... + 130 | | °C |
| V _{isol} | a. c. 50 Hz; r.m.s.; 1 s/1 min | 3600 / 3000 | | V~ |
| M ₁ | to heatsink | 5 (44 lb. in.) ± 15 % ¹⁾ | | Nm |
| M ₂ | to terminals | 9 (80 lb. in.) ± 15 % ²⁾ | | Nm |
| a | | 5 · 9,81 | | m/s ² |
| w | approx. | 400 | | g |
| Case | → page B 1 – 86 | SKKT: A 43 | SKKH: A 56 | |

¹⁾ See the assembly instructions²⁾ The screws must be lubricated

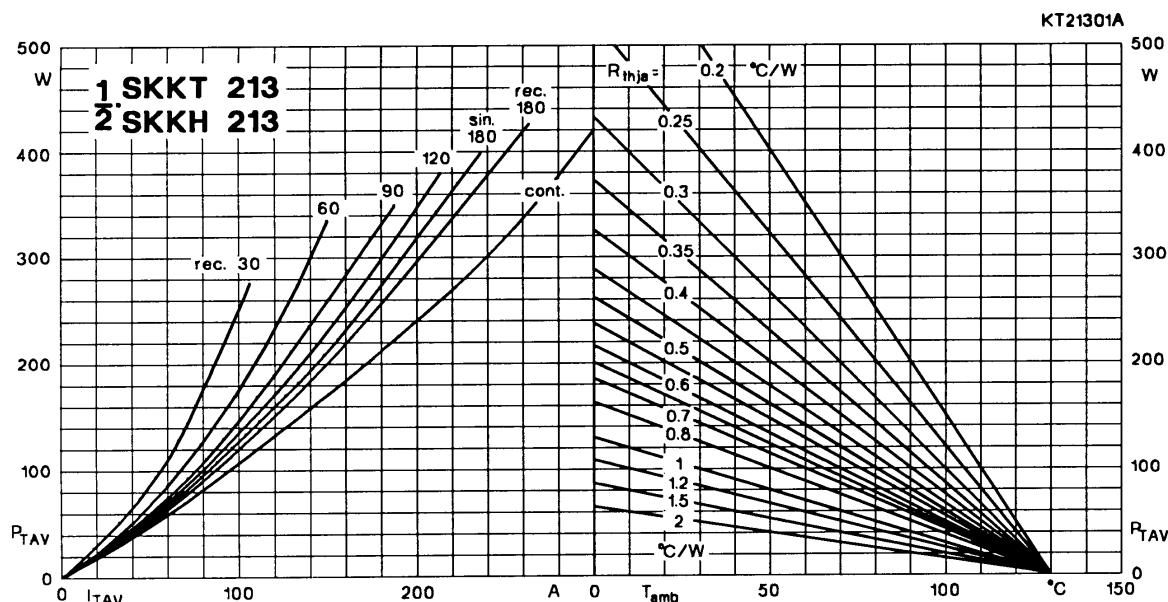


Fig. 1 a Power dissipation per thyristor vs. on-state current and ambient temperature

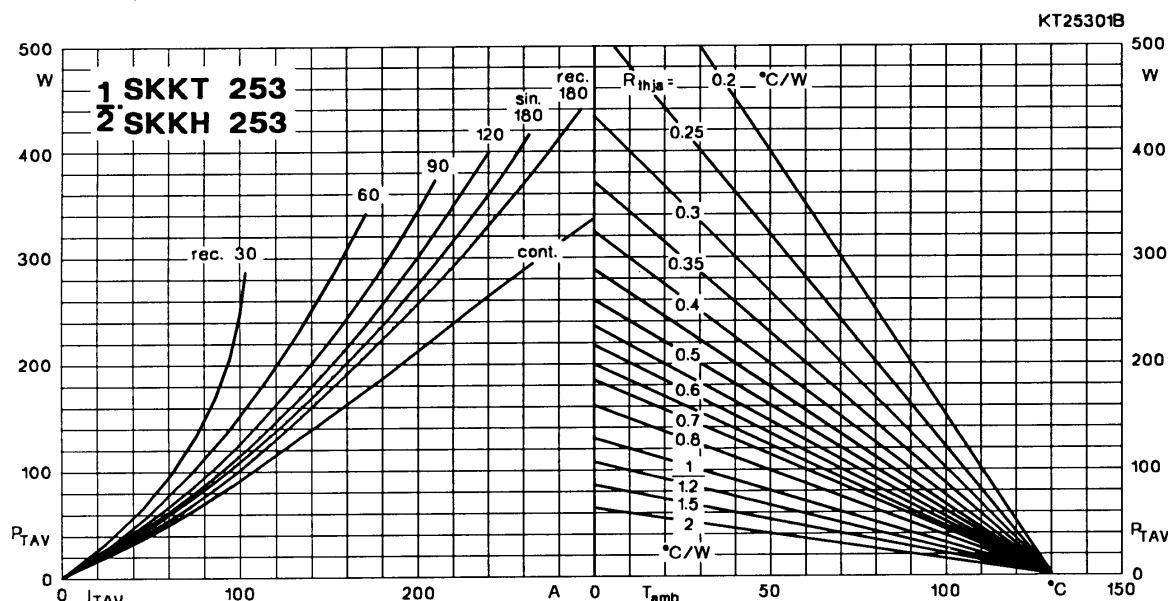


Fig. 1 b Power dissipation per thyristor vs. on-state current and ambient temperature

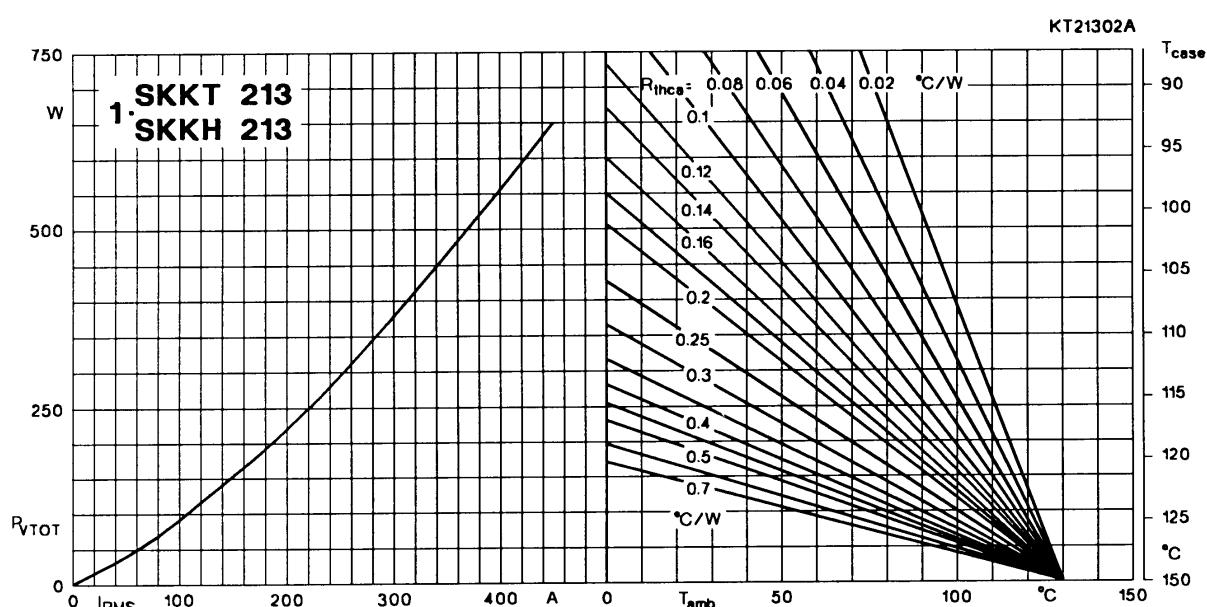


Fig. 2 a Power dissipation per module vs. rms current and case temperature

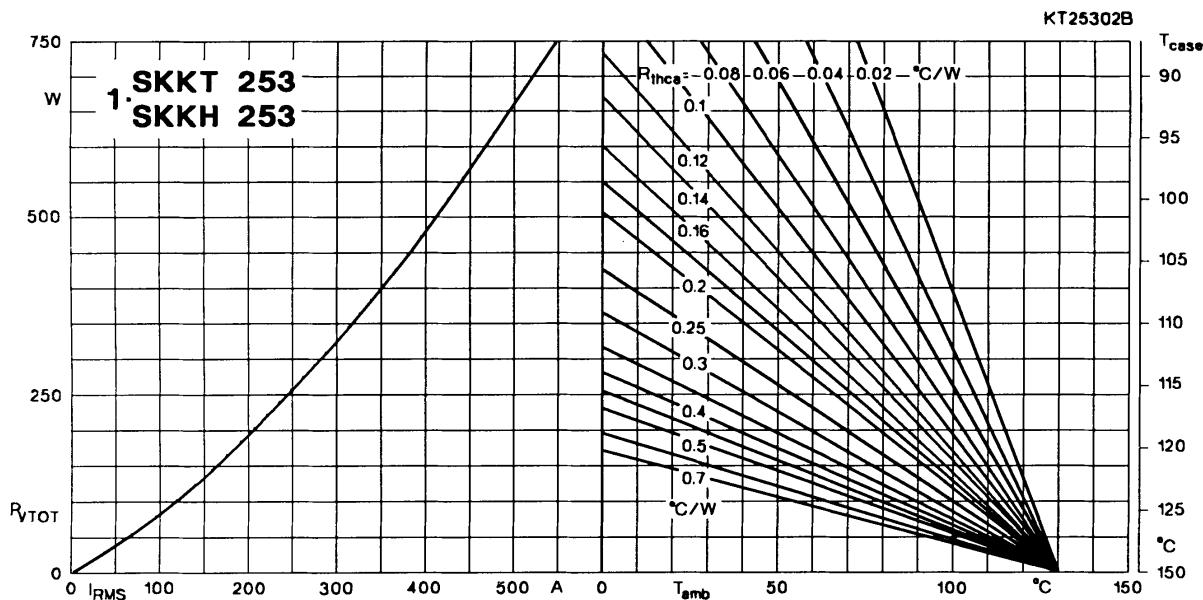


Fig. 2 b Power dissipation per module vs. rms current and case temperature

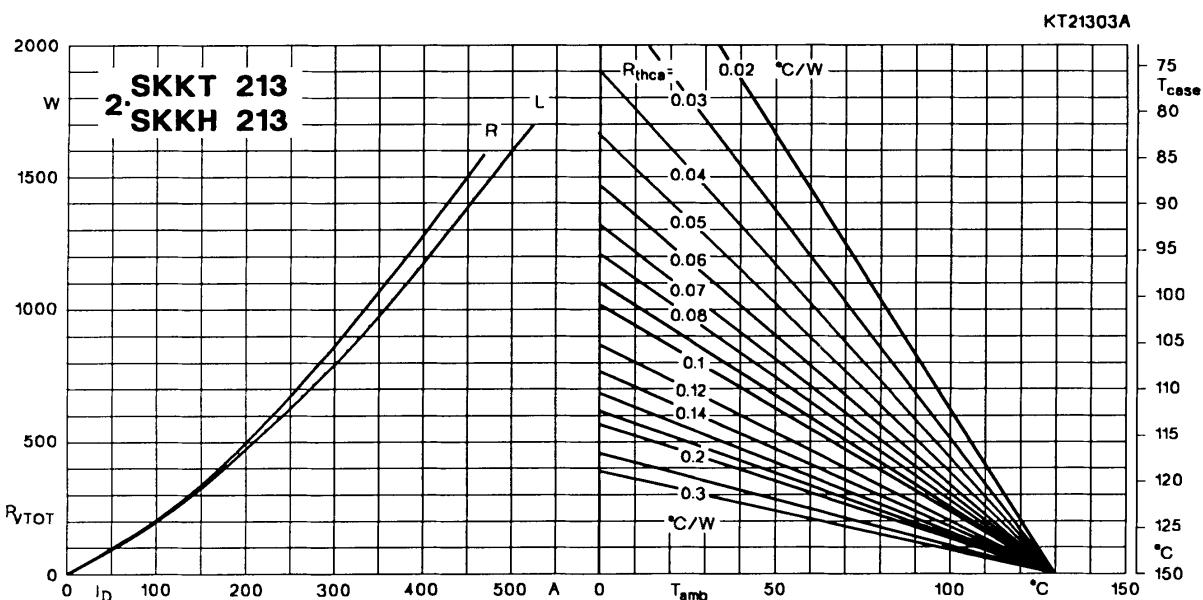


Fig. 3 a Power dissipation of two modules vs. direct current and case temperature

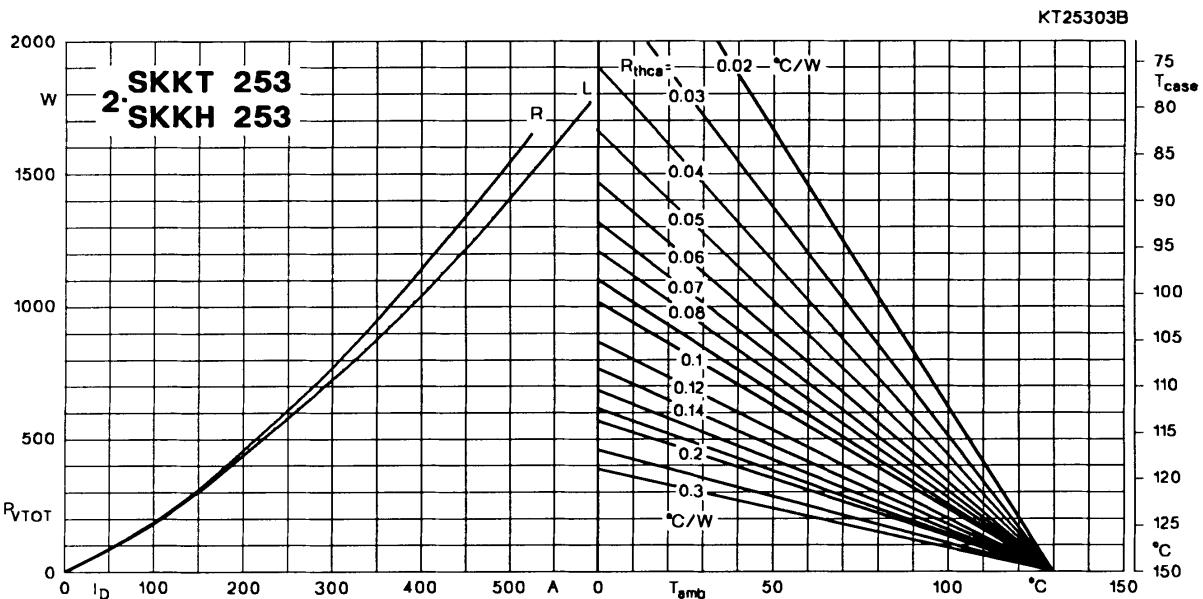


Fig. 3 b Power dissipation of two modules vs. direct current and case temperature

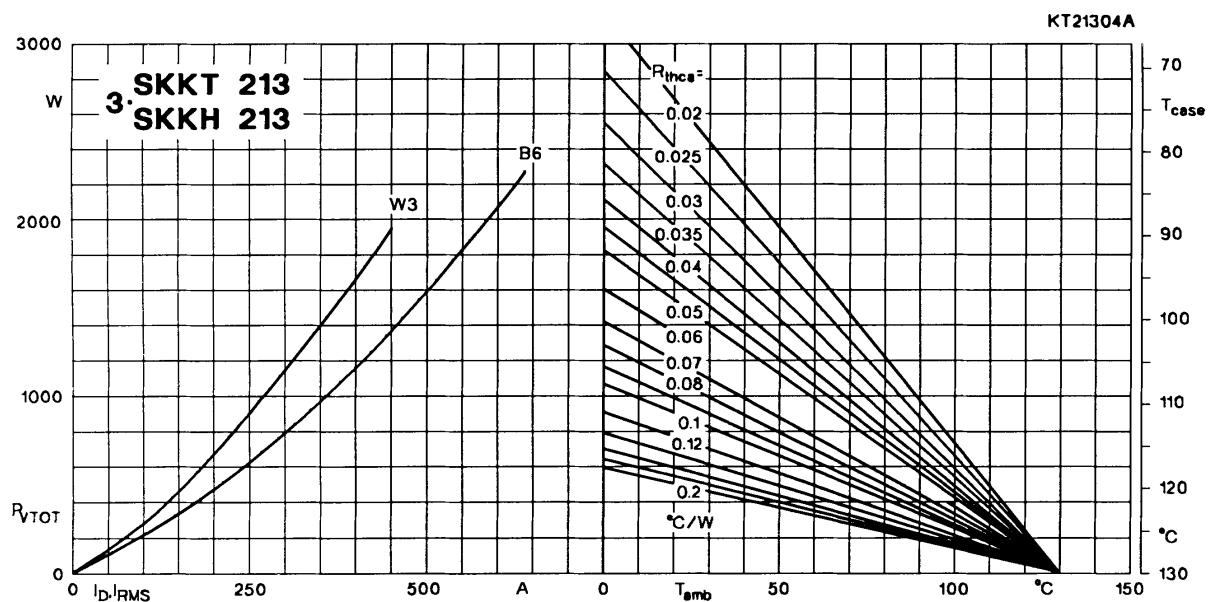


Fig. 4 a Power dissipation of three modules vs. direct and rms current and case temperature

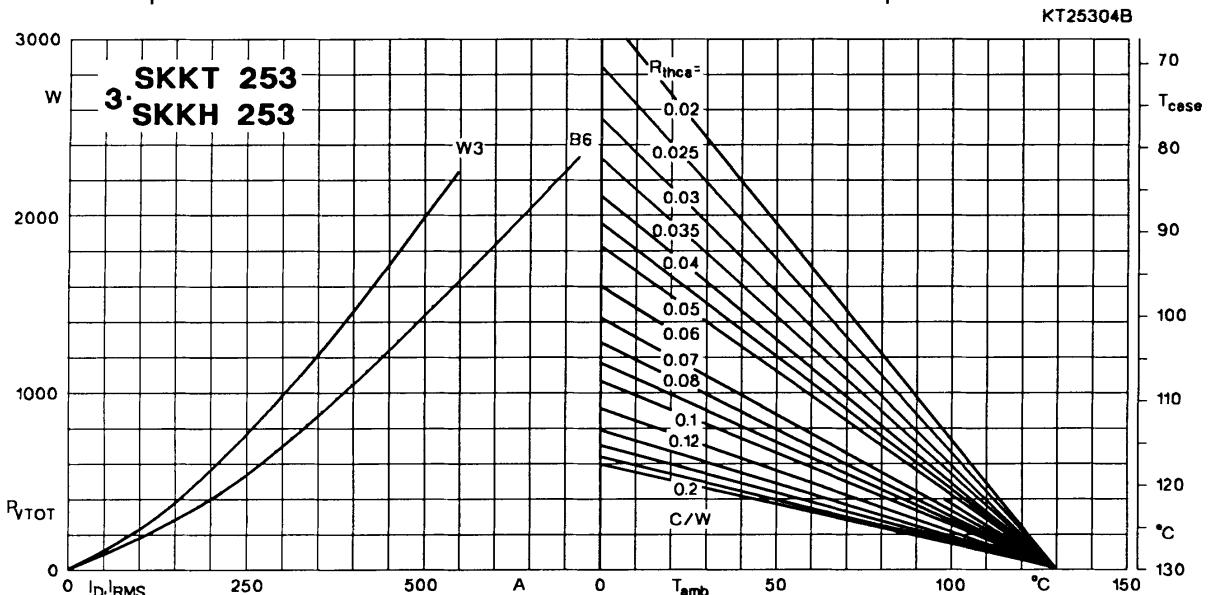


Fig. 4 b Power dissipation of three modules vs. direct and rms current and case temperature

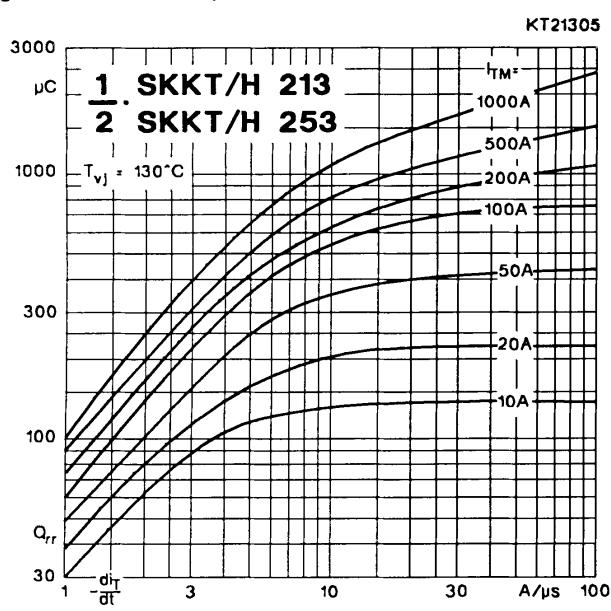


Fig. 5 Recovered charge vs. current decrease

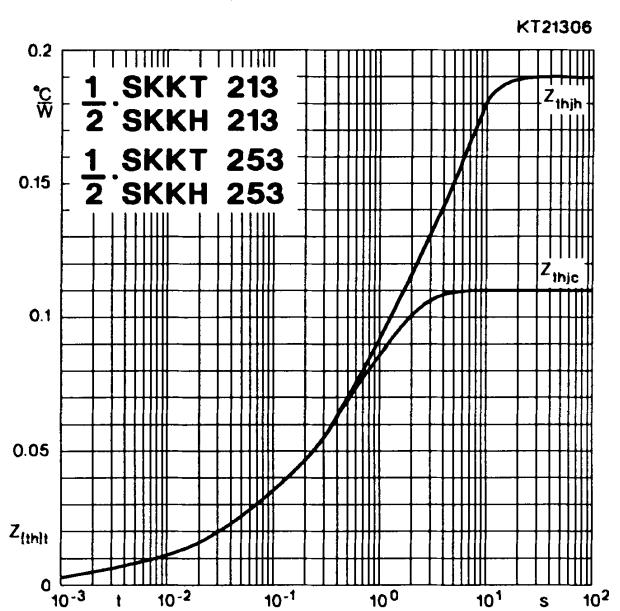


Fig. 6 Transient thermal impedance vs. time

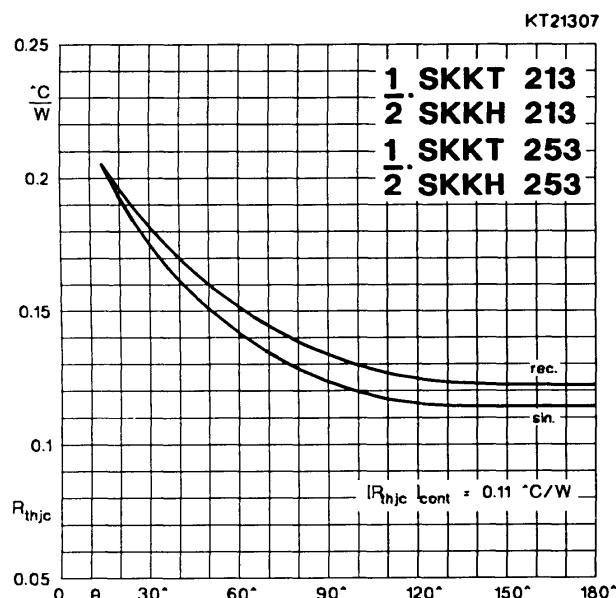


Fig. 7 Thermal resistance vs. conduction angle

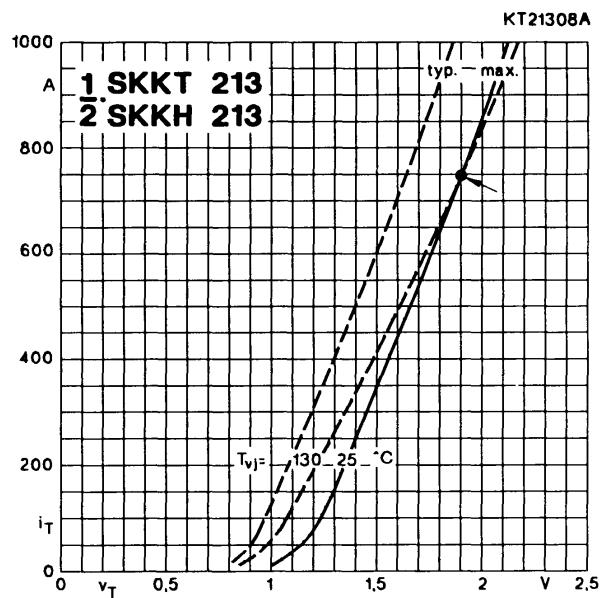


Fig. 8 a On-state characteristics

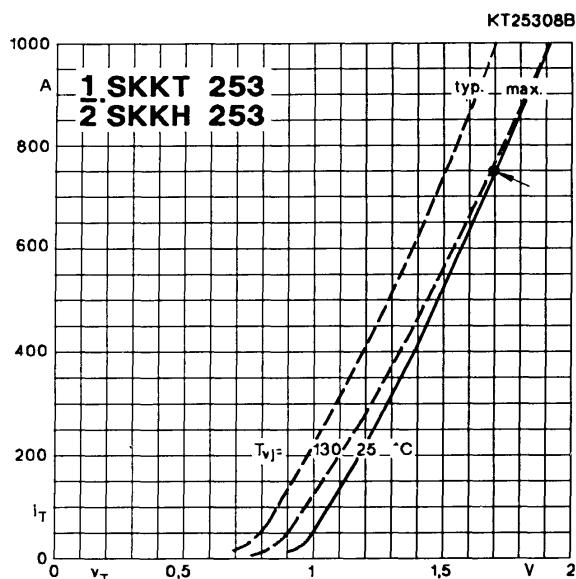


Fig. 8 b On-state characteristics

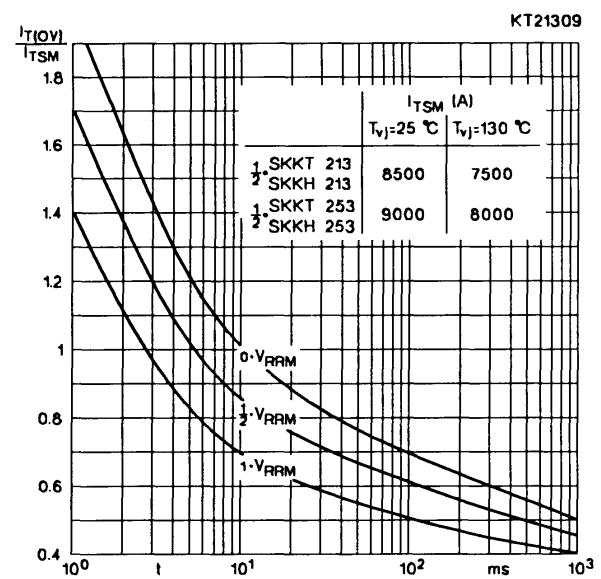


Fig. 9 Surge overload current vs. time

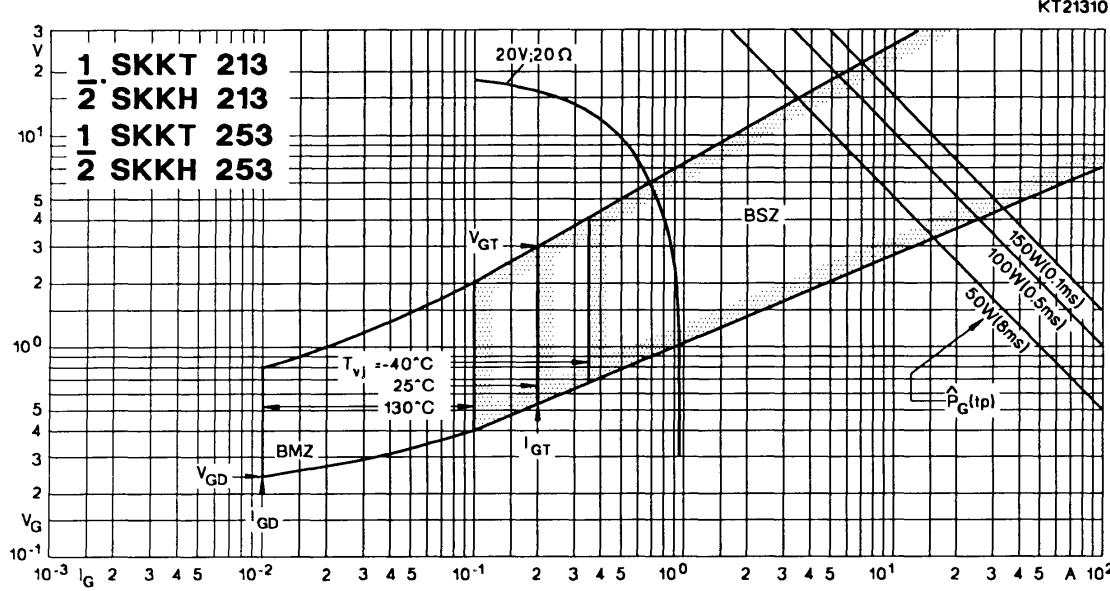
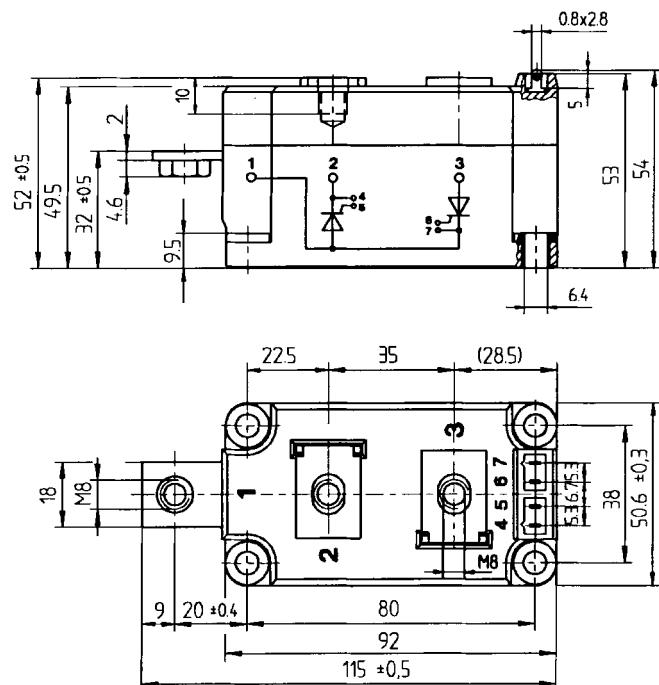


Fig. 10 Gate trigger characteristics

SKKT 213, SKKT 253

Case A 43

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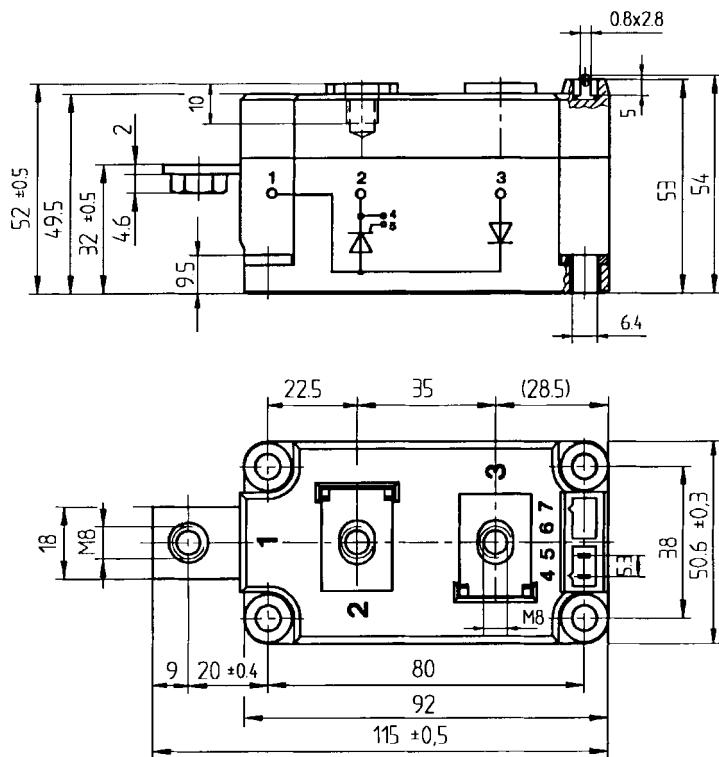


Dimensions in mm

SKKH 213, SKKH 253

Case A 56

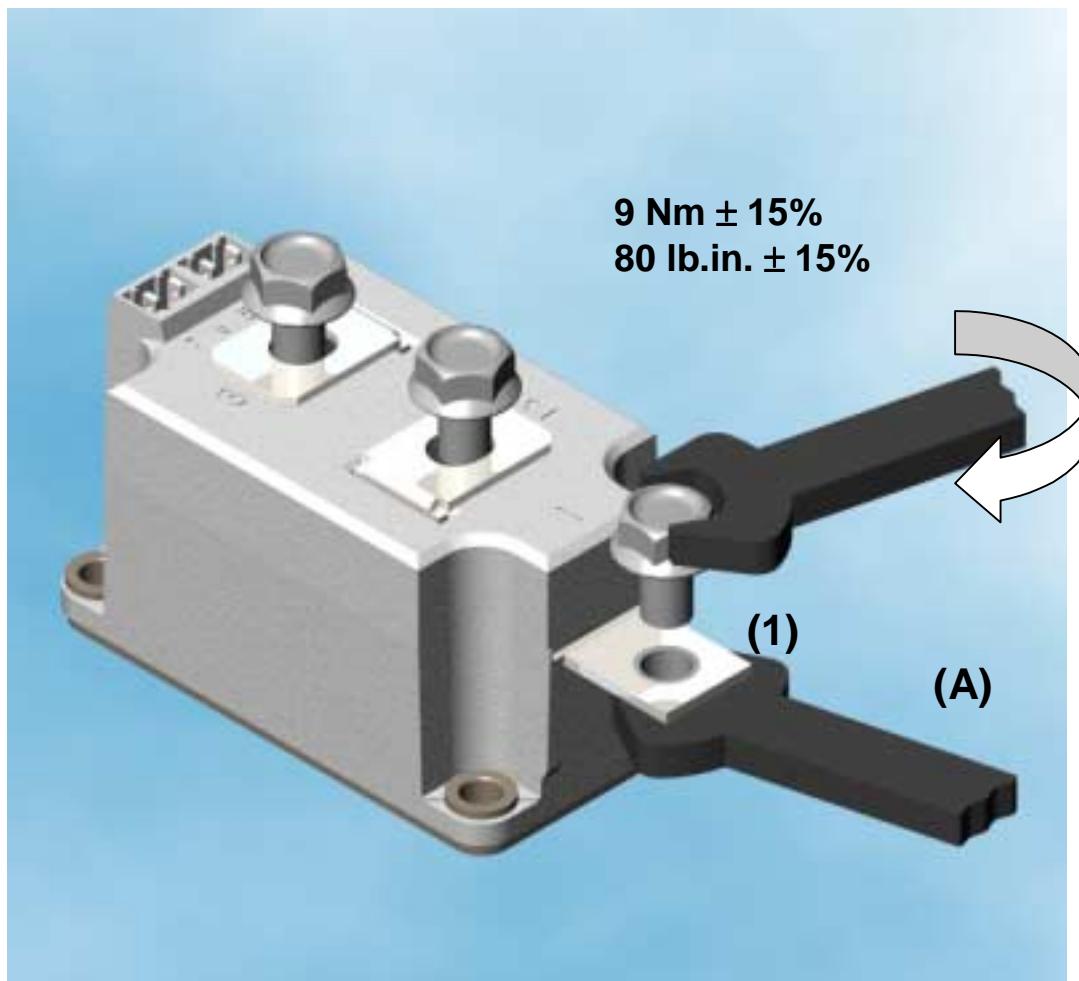
SEMIPACK® 3



Dimensions in mm

Ergänzung zu den Montagehinweisen im SEMIKRON Datenbuch

Bitte beachten Sie, daß beim Befestigen der Stromzuführung an Anschluß (1) – zur Vermeidung von Schäden am Gehäuse – die Mutter mit einem Maulschlüssel (A), gehalten werden muß.



Supplement to the Assembly Instructions in the SEMIKRON Data Book

Please note that when connecting the power supply conductor to terminal (1), a wrench (spanner) (A) should be used to restrain the nut on terminal (1) to avoid damage to the housing.